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INFORMATION DISCLOSURE
CITATION

TY. DOCKET NO.

2590-100

SE

Unknown

10/507920

APPLICANT

IONESCU et al

(Use several sheets if necessary)

FILING DATE

GROUP

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U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>[initials]</i>	4,906,586	3/1990	Blackburn	438	53	
<i>[initials]</i>	5,262,000	11/1993	Welbourn et al	156	643	
<i>[initials]</i>	6,290,864	9/2001	Patel et al	216	79	

FOREIGN PATENT DOCUMENTS

DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
<i>[initials]</i> WO 99/26333	5/1999	WIPO			

OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)

<i>[initials]</i>	Ionescu et al, "Modeling and Design of a Low-Voltage SOI Suspended-Gate MOSFET (SG-MOSFET) with a Metal-Over-Gate Architecture", PROCEEDINGS OF THE 2002 3 RD INTERNATIONAL SYMPOSIUM ON QUALITY ELECTRONIC DESIGN, March 18-21, 2002, pp. 496-501.
	Hoffman et al, "3D Structures with Piezoresistive Sensors in Standard CMOS", PROCEEDINGS OF THE WORKSHOP ON MICRO ELECTRICAL MECHANICAL SYSTEMS, January 29 - February 2, 1995, pp. 288-293.
	Devoe et al, "Surface Micromachined Piezoelectric Accelerometers (PIXLS)", JOURNAL OF MICROELECTROMECHANICAL SYSTEMS, IEEE INC., vol. 10, no. 2, June 2001, pp. 180-186.
	Chang et al, "Innovative micromachined microwave switch with very low insertion loss", SENSORS AND ACTUATORS A, ELSEVIER SEQUOIA S.A., LAUSANNE, CH, vol. 79, no. 1, January 2000, pp. 71-75.
	Pott et al, "The suspended-gate MOSFET (SG-MOSFET): a modeling outlook for the design of RF MEMS switches and tunable capacitors", 2001 INTERNATIONAL SEMICONDUCTOR CONFERENCE, CAS 2001 PROCEEDINGS (CAT. NO. 01TH8547), CAS 2001 PROCEEDINGS. 2001 INTERNATIONAL SEMICONDUCTOR CONFERENCE, SINAIA, ROMANIA, 9-13 Oct. 2001, pp. 137-140.
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<i>[initials]</i>	Meister et al, "In situ control of the electrochemical gap height modification of a suspended gate field-effect transistor by capacitance -- voltage measurement technique", SENSORS AND ACTUATORS B, ELSEVIER SEQUOIA S.A., LAUSANNE, CH, vol. 46, no. 3, 15 May 1998, pp. 226-235.

*Examiner

Date Considered

7/10/06

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.

Form PTO-FB-A820 (Also PTO-1449)